

ABSTRACT

A final polishing processing method for a heavily-doped wafer and a polished heavily-doped wafer are provided. In one aspect, the processing method includes: performing, by using a first polishing slurry, a first polishing on a heavily-doped wafer; performing, by using a second polishing slurry, a second polishing on the heavily-doped wafer on which the first polishing step has been performed; and performing, by using a third polishing slurry, a third polishing on the heavily-doped wafer on which the second polishing step has been performed, wherein the first polishing slurry and the second polishing slurry both include an alkaline additive, and the third polishing slurry does not include the alkaline additive.

(Figure 4)